

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	201	satoshi near fujimoto.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 14:23	
2	BRS	L2	2	1 and (gate near electrode)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 14:23	
3	BRS	L3	141	tsunoda near akira.in.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 14:29	
4	BRS	L4	903	438/149.ccls.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 17:00	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	1886	(gate near electrode) near15 (second near conductive)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 16:16	
6	BRS	L6	391	(gate near electrode) near15 (second near conductive near layer) near10 (first near conductive near layer)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 16:17	
7	BRS	L8	7	(gate near electrode) near15 (second near conductive near layer) near10 (first near conductive near layer) near15 (semiconductor near device) near15 (thin ot tft)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 16:18	
8	BRS	L7	53	(gate near electrode) near15 (second near conductive near layer) near10 (first near conductive near layer) near15 (semiconductor near device)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 16:20	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	137	(impurity near region) near10 (concentration near distribution)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/17 17:02	
10	BRS	L10	4	(impurity near region) near10 (concentration near distribution) near15 (increas\$2 near5 distance)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/17 17:04	
11	BRS	L11	14	(impurity) near10 (concentration near distribution) near15 (increas\$2 near5 distance)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/17 17:04	
12	BRS	L12	14	(impurity) near10 (concentration near distribution) near15 (increas\$2 near3 distance)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/17 17:07	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	9	(impurity) near10 (concentration near distribution) near15 (distance) near15 (channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/01/17 17:19	
14	BRS	L14	0	(concentration near distribution) near15 (exponetial near distribution)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/01/17 17:21	
15	BRS	L15	0	(concentration near distribution) near15 (exponetial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/01/17 17:21	
16	BRS	L16	0	(concentration) near15 (exponetial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2004/01/17 17:21	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
17	BRS	L17	1265	(concentration) near15 (exponential)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 17:21	
18	BRS	L18	15	(concentration near distribution) near15 (exponential)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 17:21	
19	BRS	L20	0	(concentration near distribution) near15 (exponential near distribution) near15 (semiconductor)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 17:22	
20	BRS	L19	10	(concentration near distribution) near15 (exponential near distribution)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/01/1 7 17:22	

	U	I	PT	P	Document ID	Issue Date	Pages	Title
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030096460 A1	20030522	43	Method of manufacturing semiconductor devices
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030094614 A1	20030522	29	Semiconductor device and method of manufacturing the same
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020110941 A1	20020815	36	Semiconductor device and manufacturing method thereof
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020089616 A1	20020711	15	Thin film semiconductor device and liquid crystal display unit, and fabrication methods thereof
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6587165 B2	20030701	15	Thin film semiconductor device and liquid crystal display unit, and fabrication methods thereof
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6518594 B1	20030211	43	Semiconductor devices
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6501098 B2	20021231	56	Semiconductor device